

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
22 June 2006 (22.06.2006)

PCT

(10) International Publication Number
WO 2006/064822 A1

(51) International Patent Classification:
H03K 19/0175 (2006.01)

(21) International Application Number:
PCT/JP2005/022901

(22) International Filing Date:
7 December 2005 (07.12.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2004-360636 13 December 2004 (13.12.2004) JP

(71) Applicant (for all designated States except US): SEMI-
CONDUCTOR ENERGY LABORATORY CO., LTD.
[JP/JP]; 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP).

(72) Inventors; and

(75) Inventors/Applicants (for US only): OSAME, Mitsuaki
[JP/JP]; c/o SEMICONDUCTOR ENERGY LABORA-
TORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa,
2430036 (JP). IWABUCHI, Tomoyuki. KIMURA,
Hajime.

(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AF, AG, AI, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CI, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KM, KN, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV,
LY, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI,
NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG,
SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US,
UZ, VC, VN, YU, ZA, ZM, ZW.

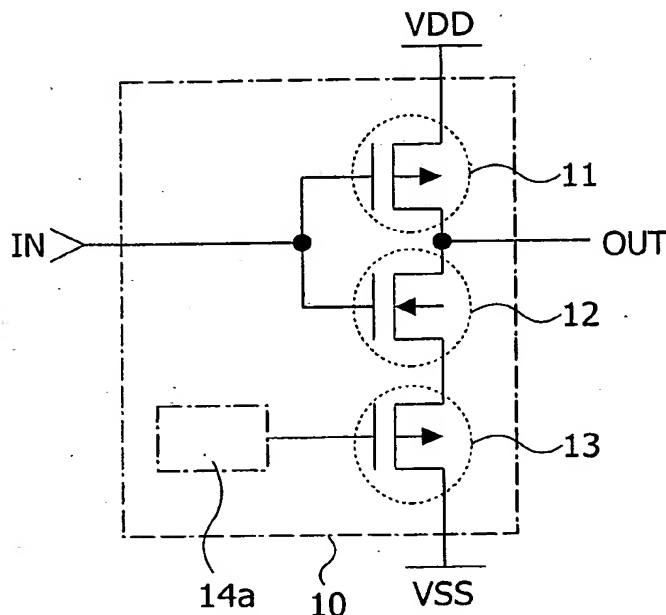
(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SI, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT,
RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA,
GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: SEMICONDUCTOR DEVICE AND ELECTRONIC APPLIANCE USING THE SAME



(57) Abstract: A semiconductor device with less power consumption and an electronic appliance using the same. The semiconductor device of the invention is supplied with a first potential from a high potential power source and a second potential from a low potential power source. Upon input of a first signal to an input node, an output node outputs a second signal. With the semiconductor device of the invention, a potential difference of the second signal can be controlled to be smaller than a potential difference between the first potential and the second potential, thereby power consumption required for charging/discharging wires can be reduced.

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